



SI4162DY-T1-GE3 Information



For Reference Only

Part Number SI4162DY-T1-GE3 **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 19.3A 8-SOIC **Package** 8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SI4162DY-T1-GE3 Specifications

Manufacturer Part Number SI4162DY-T1-GE3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Ourrent - Continuous Drain (Id) @ 25°C 19.3A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1155pF @ 15V Vgs (Max) Vgs (Max) **ET Feature** Power Dissipation (Max) Rds On (Max) @ Id, Vgs Test Feature Power Dissipation (Max) Supplier Device Package Package / Case **BOIC (0.154", 3.90mm Width)	Manufacturer Part Number	SI4162DY-T1-GE3
Package 8-SOIC (0.154", 3.90mm Width) Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 19.3A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 30nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1155pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 5W (Tc) Rds On (Max) @ Id, Vgs 7.9 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Manufacturer	Vishay Siliconix
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C19.3A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs30nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1155pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 5W (Tc)Rds On (Max) @ Id, Vgs7.9 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Series	TrenchFET?
Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C19.3A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs30nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1155pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 5W (Tc)Rds On (Max) @ Id, Vgs7.9 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.9 mOhm @ 20A, 10V Operating Temperature Supplier Device Package Package / Case 19.3A (Tc) 19.3F (Tc) 19.3A (Tc) 19.3C (Tu) 19.3A (Tc) 19.3C (Tu) 19.3A (Tc) 19.3A (Tc) 19.3A (Tc) 19.3A (Tc) 19.3C (Tu) 19.3A (Tc) 19.3A (Tc) 19.3C (Tu) 19.3A (Tc) 19.3C (Tu) 19.3A (Tc) 19.3C (Tu) 19.3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs30nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1155pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 5W (Tc)Rds On (Max) @ Id, Vgs7.9 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 30nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1155pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 5W (Tc) Rds On (Max) @ Id, Vgs 7.9 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	19.3A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1155pF @ 15V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.9 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.9 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	3V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 5W (Tc)Rds On (Max) @ Id, Vgs7.9 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	30nC @ 10V
FET Feature - Power Dissipation (Max) 2.5W (Ta), 5W (Tc) Rds On (Max) @ Id, Vgs 7.9 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Input Capacitance (Ciss) (Max) @ Vds	1155pF @ 15V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.9 mOhm @ 20A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs7.9 mOhm @ 20A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	2.5W (Ta), 5W (Tc)
Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	7.9 mOhm @ 20A, 10V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

SI4162DY-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SI4162DY-T1-GE3 Payment Methods



















SI4162DY-T1-GE3 Shipping Methods













If you have any question about SI4162DY-T1-GE3, please do not hesitate to contact us!

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